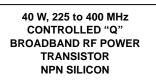
# The RF Line NPN Silicon RF Power Transistor

 $\ldots$  designed primarily for wideband large–signal output amplifier stages in the 100 to 500 MHz frequency range.

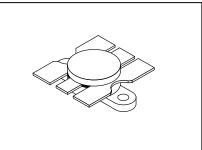
- Guaranteed Performance @ 400 MHz, 28 Vdc Output Power = 40 Watts Minimum Gain = 9.0 dB
- Built-In Matching Network for Broadband Operation
- 100% Tested for Load Mismatch at all Phase Angles with 30:1 VSWR
- Gold Metallization System for High Reliability Applications

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	33	Vdc
Collector–Base Voltage	V <sub>CBO</sub>	60	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current — Continuous — Peak	IC	4.5 6.0	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C (1) Derate above 25°C	PD	110 0.63	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C



**MRF326** 



CASE 316-01, STYLE 1

# THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Case	R <sub>θ</sub> JC	1.6	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	·		•		
Collector–Emitter Breakdown Voltage $(I_{C} = 40 \text{ mAdc}, I_{B} = 0)$	V <sub>(BR)</sub> CEO	33	-	-	Vdc
Collector–Emitter Breakdown Voltage $(I_{C} = 40 \text{ mAdc}, V_{BE} = 0)$	V(BR)CES	60	-	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 4.0 \text{ mAdc}, I_C = 0$ )	V <sub>(BR)EBO</sub>	4.0	-	-	Vdc
Collector–Base Breakdown Voltage $(I_{C} = 40 \text{ mAdc}, I_{E} = 0)$	V <sub>(BR)</sub> CBO	60	-	-	Vdc
Collector Cutoff Current ( $V_{CB} = 30 \text{ Vdc}, I_E = 0$ )	ICBO	_	-	4.0	mAdc
ON CHARACTERISTICS			•		
DC Current Gain (I <sub>C</sub> = 2.0 Adc, $V_{CE}$ = 5.0 Vdc)	hFE	20	50	80	-
DYNAMIC CHARACTERISTICS	•		•	•	•
Output Capacitance	C <sub>ob</sub>	_	45	60	pF

NOTE:

1. This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier.



(V<sub>CB</sub> = 28 Vdc, I<sub>E</sub> = 0, f = 1.0 MHz)

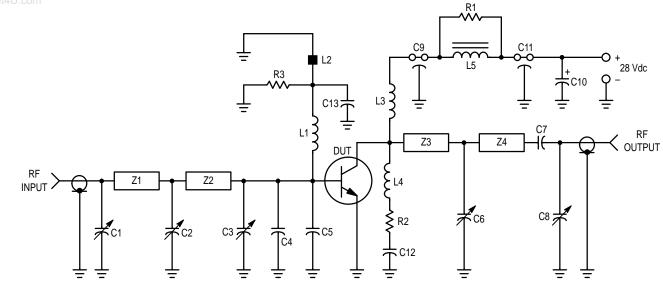


(continued)

# **ELECTRICAL CHARACTERISTICS** — continued ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
FUNCTIONAL TESTS (Figure 1)					
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 40 W, f = 400 MHz, I <sub>C</sub> Max = 2.85 Adc)	GPE	9.0	11	—	dB
Collector Efficiency (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 40 W, f = 400 MHz, I <sub>C</sub> Max = 2.85 Adc)	η	50	_	—	%
Load Mismatch (V <sub>CC</sub> = 28 Vdc, P <sub>OUt</sub> = 40 W CW, f = 400 MHz, VSWR = 30:1 All Phase Angles)	Ψ	No Degradation in Output Power			

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- C1 1.0–10 pF Johanson, Capacitor (JMC 5201) C2, C3, C6, C8 — 1.0–20 pF Johanson Capacitor C4, C5 — 36 pF ATC "B" Style Chip Capacitor C7, C9, C13 — 100 pF UNELCO Capacitor C11 — 680 pF Feedthru C10 — 1.0  $\mu$ F 50 V Tantalum
- C12 0.1 µF Erie Redcap
- L1 8 Turns #26 AWG Enameled, 1/16" ID Closewound
- L2, L5 Ferroxcube VK200–19/4B Ferrite Choke
- $\begin{array}{l} {\sf L3} = 8 \; {\sf Turns} \; \text{\#20} \; {\sf AWG} \; {\sf Enameled}, \; 1/4'' \; {\sf ID} \; {\sf Closewound} \\ {\sf L4} = 4 \; {\sf Turns} \; \text{\#26} \; {\sf AWG} \; 0.1'' \; {\sf ID} \\ {\sf R1} = 10 \; {\sf Ohm} \; 2.0 \; {\sf W} \; {\sf Carbon} \\ {\sf R2}, \; {\sf R3} = 10 \; {\sf Ohm} \; 1.0 \; {\sf W} \; {\sf Carbon} \\ {\sf Z1} = \; {\sf Microstrip} \; 0.19'' \; {\sf W} \; {\sf x} \; 1.28'' \; {\sf L} \\ {\sf Z2} = \; {\sf Microstrip} \; 0.28'' \; {\sf W} \; {\sf x} \; 1.0'' \; {\sf L} \\ {\sf Z3} = \; {\sf Microstrip} \; 0.31'' \; {\sf W} \; {\sf x} \; 1.0'' \; {\sf L} \\ {\sf Z4} = \; {\sf Microstrip} \; 0.31'' \; {\sf W} \; {\sf x} \; 0.9'' \; {\sf L} \\ {\sf Board} = \; {\sf Glass} \; {\sf Teflon} \; {\sf \epsilon_f} = 2.56 \; {\sf t} = 0.062''' \\ {\sf Input/Output} \; {\sf Connectors} = \; {\sf Type} \; {\sf N} \; {\sf UG58} \; {\sf A/U} \\ \end{array}$

Figure 1. 400 MHz Test Amplifier

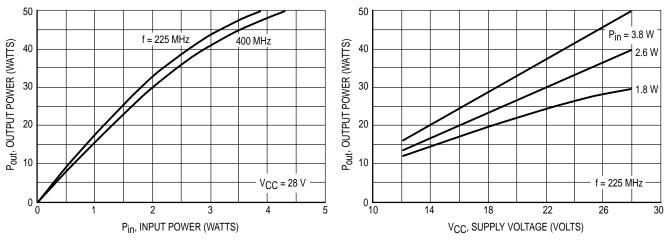


Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Supply Voltage

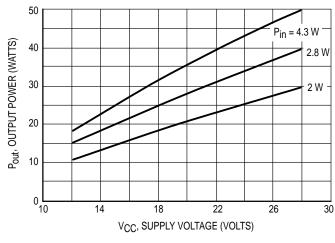
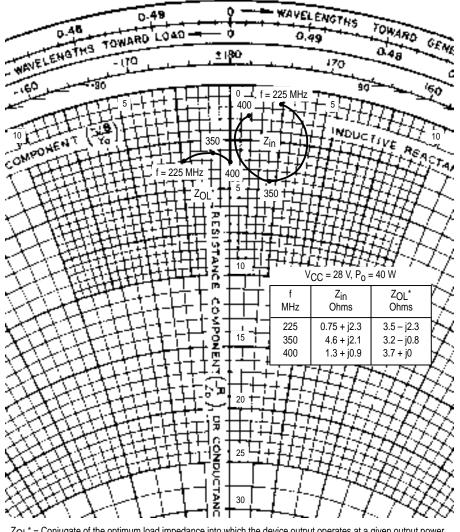


Figure 4. Output Power versus Supply Voltage f = 400 MHz

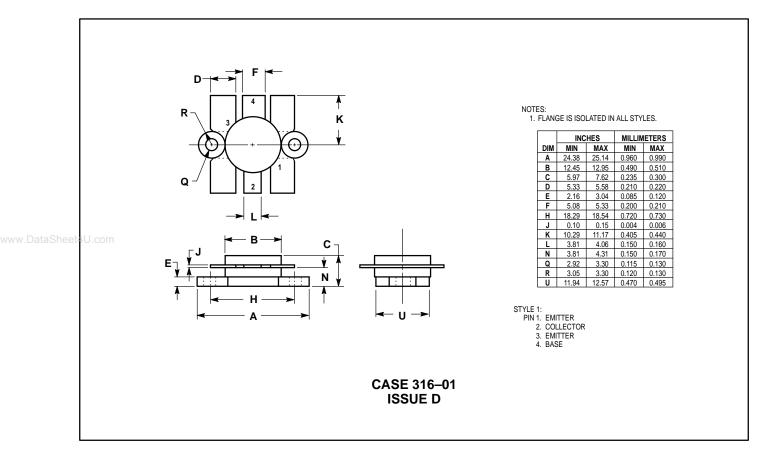


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Z<sub>OL</sub>\* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 5. Series Equivalent Input–Output Impedance

# PACKAGE DIMENSIONS



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